

Nanoparticle Assemblies as Memristors

[*Nano Lett.* **2009**, *9*, 2229]

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Pages 2229–2233. Upon our continued investigation of the switching behaviors after its publication, problems associated with the instrument in the high resistance regime that we used for the V – I measurements were discovered. Those hysteresis results that are presented in Figure 1, Figure 2, Figure 4, and Supporting Information Figure S3 are strongly caused by the faulty fluctuation from the instrument when the resistance becomes higher than 200 M Ω . Such a problem is highly dependent on the operating mode of the instrument and appears during the voltage range change from 10 to 100 V.

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Interplay between Ferroelastic and Metal–Insulator Phase Transitions in Strained Quasi-Two-Dimensional VO₂ Nanoplatelets

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Alexander Tselev,* Evgheni Strelcov, Igor A. Luk'yanchuk, John D. Budai, Jonathan Z. Tischler, Ilia N. Ivanov, Keith Jones, Roger Proksch, Sergei V. Kalinin, and Andrei Kolmakov*

Page 2010. Equation 6 appeared incorrect. The correct eq 6 is

$$t'_{c1} = \frac{3}{16}t_0(1 - \lambda)(1 + 3\lambda), \quad t'_{c2} = \frac{3}{16}t_0(1 - \lambda)^2 \quad (6)$$

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